



STC03DE220HP

Hybrid emitter switched bipolar transistor

ESBT[®] 2200 V - 3 A - 0.33 Ω

Preliminary Data

Features

Table 1. Features

$V_{CS(ON)}$	I_C	$R_{CS(ON)}$
1V	3A	0.33Ω

- Low equivalent on resistance
- Very fast-switch, up to 150 kHz
- Very low C_{ISS} driven by $R_G = 4.7 \Omega$

Applications

- Aux SMPS for three phase mains

Description

The STC03DE220HP is manufactured in a hybrid structure, using dedicated high voltage Bipolar and low voltage MOSFET technologies, aimed to providing the best performance in ESBT topology. The STC03DE220HP is designed for use in aux flyback SMPS for any three phase application.

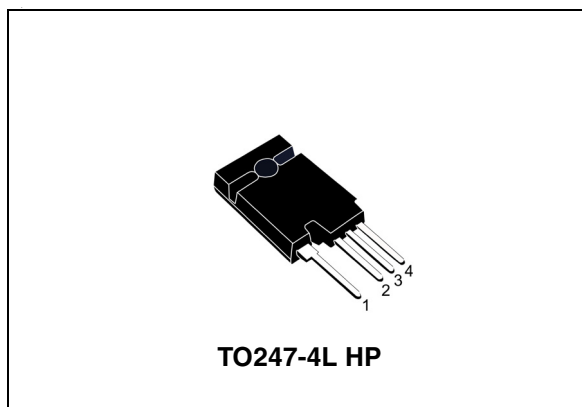


Figure 1. Internal schematic diagrams

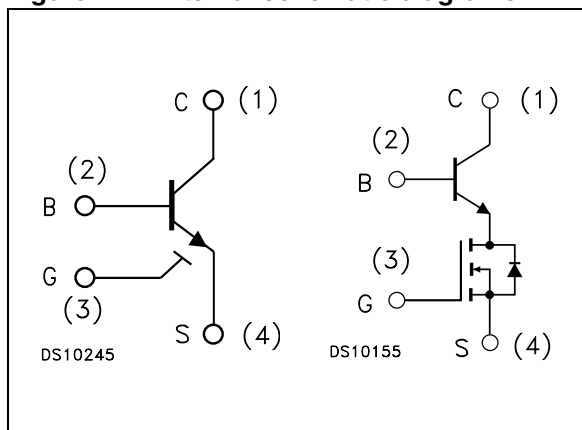


Table 2. Device summary

Order code	Marking	Package	Packaging
STC03DE220HP	C03DE220HP	TO247-4L HP	Tube

1 Electrical ratings

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{CS(SS)}$	Collector-source voltage ($V_{BS} = V_{GS} = 0$)	2200	V
$V_{BS(OS)}$	Base-source voltage ($I_C = 0, V_{GS} = 0$)	30	V
$V_{SB(OS)}$	Source-base voltage ($I_C = 0, V_{GS} = 0$)	9	V
V_{GS}	Gate-source voltage	± 20	V
I_C	Collector current	3	A
I_{CM}	Collector peak current ($t_P < 5$ ms)	6	A
I_B	Base current	3	A
I_{BM}	Base peak current ($t_P < 1$ ms)	6	A
P_{tot}	Total dissipation at $T_c \leq 25$ °C	tbd	W
T_{stg}	Storage temperature	-40 to 150	°C
T_J	Max. operating junction temperature	125	°C

Table 4. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	tbd	°C/W

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified)

Table 5. Electrical characteristics

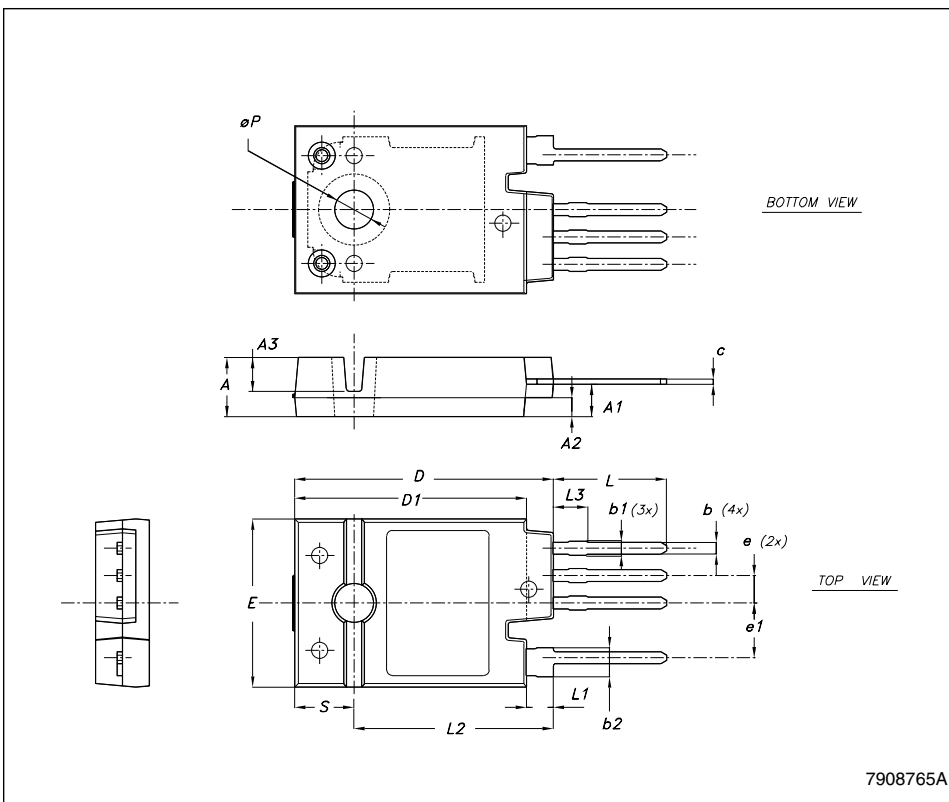
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CS(SS)}}$	Collector-source current ($V_{\text{BS}} = V_{\text{GS}} = 0$)	$V_{\text{CS(SS)}} = 2200\text{ V}$			100	μA
$I_{\text{BS(OS)}}$	Base-source current ($I_{\text{C}} = 0, V_{\text{GS}} = 0$)	$V_{\text{BS(OS)}} = 30\text{ V}$			10	μA
$I_{\text{SB(OS)}}$	Source-base current ($I_{\text{C}} = 0, V_{\text{GS}} = 0$)	$V_{\text{SB(OS)}} = 9\text{ V}$			100	μA
$I_{\text{GS(OS)}}$	Gate-source leakage ($V_{\text{BS}} = 0$)	$V_{\text{GS}} = \pm 20\text{ V}$			500	nA
$V_{\text{CS(ON)}}$	Collector-source ON voltage	$V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 1.5\text{ A } I_{\text{B}} = 0.15\text{ A}$ $V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 3\text{ A } I_{\text{B}} = 0.6\text{ A}$		0.2 0.25		V V
h_{FE}	DC current gain	$V_{\text{CS}} = 1\text{ V } V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 1.5\text{ A}$ $V_{\text{CS}} = 1\text{ V } V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 3\text{ A}$		15 10		
$V_{\text{BS(ON)}}$	Base-source ON voltage	$V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 1.5\text{ A } I_{\text{B}} = 0.15\text{ A}$ $V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 3\text{ A } I_{\text{B}} = 0.6\text{ A}$		0.82 1		V V
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{BS}} = V_{\text{GS}} \quad I_{\text{B}} = 250\text{ }\mu\text{A}$	1.5	2.2	3	V
C_{iss}	Input capacitance ($V_{\text{GS}} = V_{\text{CB}} = 0$)	$V_{\text{CS}} = 25\text{ V } f = 1\text{ MHz}$		750		pF
$Q_{\text{GS(tot)}}$	Gate-source Charge ($V_{\text{CB}} = 0$)	$V_{\text{CS}} = 15\text{ V } V_{\text{GS}} = 10\text{ V}$ $I_{\text{C}} = 1.8\text{ A}$		12.5		nC
t_{s} t_{f}	INDUCTIVE LOAD Storage time Fall time	$V_{\text{GS}} = 10\text{ V} \quad R_{\text{G}} = 47\text{ }\Omega$ $V_{\text{Clamp}} = 1760\text{ V} \quad t_{\text{p}} = 4\text{ }\mu\text{s}$ $I_{\text{C}} = 1.5\text{ A} \quad I_{\text{B}} = 0.3\text{ A}$		1040 20		ns ns
$V_{\text{CS(dyn)}}$	Collector-source dynamic voltage (500 ns)	$V_{\text{CC}} = V_{\text{Clamp}} = 400\text{ V}$ $V_{\text{GS}} = 10\text{ V} \quad I_{\text{C}} = 1.5\text{ A}$ $I_{\text{B}} = 0.3\text{ A} \quad R_{\text{G}} = 47\text{ }\Omega$ $t_{\text{peak}} = 500\text{ ns} \quad I_{\text{Bpeak}} = 3\text{ A}$		7.6		V
$V_{\text{CS(dyn)}}$	Collector-source dynamic voltage (1 μs)	$V_{\text{CC}} = V_{\text{Clamp}} = 400\text{ V}$ $V_{\text{GS}} = 10\text{ V} \quad I_{\text{C}} = 1.5\text{ A}$ $I_{\text{B}} = 0.3\text{ A} \quad R_{\text{G}} = 47\text{ }\Omega$ $t_{\text{peak}} = 500\text{ ns} \quad I_{\text{Bpeak}} = 3\text{ A}$		5.8		V
V_{CSW}	Maximum collector-source voltage switched without snubber	$R_{\text{G}} = 47\text{ }\Omega \quad h_{\text{FE}} = 5 \quad I_{\text{C}} = 3\text{ A}$	2200			V

3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : www.st.com

TO247-4L HP mechanical data

DIM.	mm.		
	MIN.	TYP.	MAX.
A	5.50	5.65	5.80
A1	2.85	3.15	3.25
A2		1.92	
A3		3.18	
b	0.95	1.10	1.30
b1	1.10		1.50
b2	2.50		2.90
c	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
e		2.54	
e1		5.08	
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
øP	3.55		3.65
S		5.50	



4 Revision history

Table 6. Document revision history

Date	Revision	Changes
19-May-2008	1	First release.

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